STU/D413S

SamHop Microelectronics Corp.

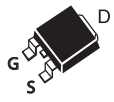
Ver 1.0

P-Channel Logic Level Enhancement Mode Field Effect Transistor

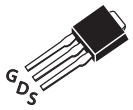
PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
-40V	-19A	48 @ VGS=10V
		78 @ VGS=4.5V

FEATURES

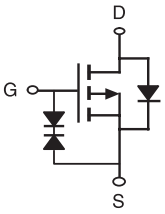
- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- Suface Mount Package.
- ESD Protected.



STU SERIES
TO-252AA(D-PAK)



STD SERIES
TO-251(I-PAK)



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V_{DS}	Drain-Source Voltage		-40	V
V_{GS}	Gate-Source Voltage		±20	V
I_D	Drain Current-Continuous [a]	T_C=25°C	-19	A
		T_C=70°C	-15	A
I_{DM}	-Pulsed [b]		-58	A
E_{AS}	Sigle Pulse Avalanche Energy [d]		16	mJ
P_D	Maximum Power Dissipation [a]	T_C=25°C	32	W
		T_C=70°C	20	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C

THERMAL CHARACTERISTICS

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case [a]	4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient [a]	50	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-40			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-32V , V_{GS}=0V			1	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V , V_{DS}=0V			±10	uA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_D=-250uA	-1	-1.8	-3	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=-10V , I_D=-9.5A		38	48	m ohm
		V_{GS}=-4.5V , I_D=-7.5A		58	78	m ohm
g_{FS}	Forward Transconductance	V_{DS}=-10V , I_D=-9.5A		10		S
DYNAMIC CHARACTERISTICS [c]						
C_{ISS}	Input Capacitance	V_{DS}=-20V,V_{GS}=0V f=1.0MHz		895		pF
C_{OSS}	Output Capacitance			138		pF
C_{RSS}	Reverse Transfer Capacitance			67		pF
SWITCHING CHARACTERISTICS [c]						
$t_{D(ON)}$	Turn-On Delay Time	V_{DD}=-20V I_D=-1.0A V_{GS}=-10V R_{GEN}=3.3 ohm		14		ns
tr	Rise Time			14		ns
$t_{D(OFF)}$	Turn-Off Delay Time			54		ns
tf	Fall Time			10		ns
Q_g	Total Gate Charge	V_{DS}=-20V,I_D=-9.5A,V_{GS}=-10V		14.5		nC
		V_{DS}=-20V,I_D=-9.5A,V_{GS}=-4.5V		7		nC
Q_{gs}	Gate-Source Charge	V_{DS}=-20V,I_D=-9.5A, V_{GS}=-10V		2.1		nC
Q_{gd}	Gate-Drain Charge			3.4		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Is	Maximum Continuous Drain-Source Forward Current				-2.0	A
V_{SD}	Diode Forward Voltage [b]	V_{GS}=0V,I_S= -2.0A		-0.77	-1.3	V

Notes

a.Surface Mounted on FR4 Board,t ≤ 10sec.

b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.

c.Guaranteed by design, not subject to production testing.

d.Starting T_J=25°C,L=0.5mH,V_{DD} = 20V .(See Figure13)

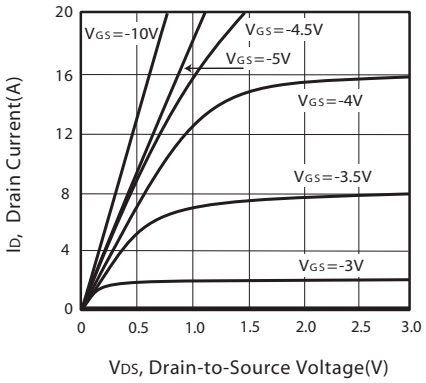


Figure 1. Output Characteristics

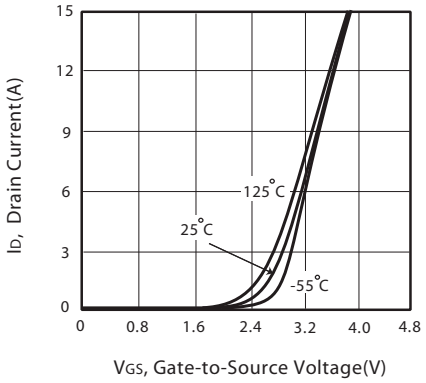


Figure 2. Transfer Characteristics

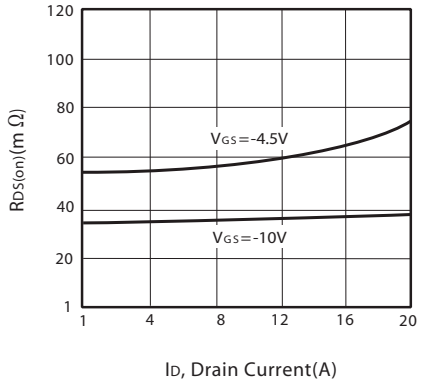


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

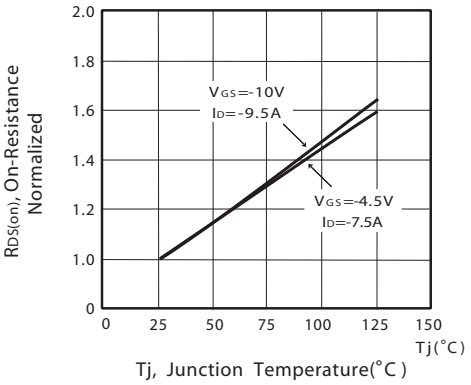


Figure 4. On-Resistance Variation with Drain Current and Temperature

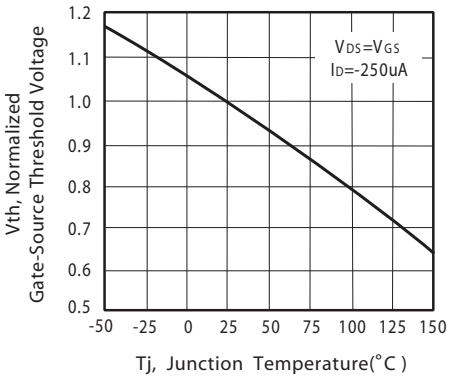


Figure 5. Gate Threshold Variation with Temperature

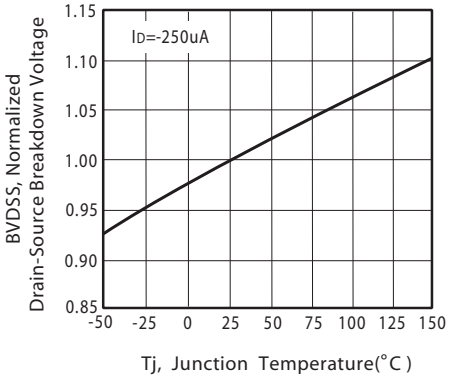


Figure 6. Breakdown Voltage Variation with Temperature

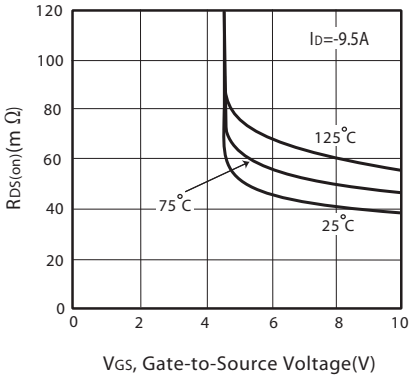


Figure 7. On-Resistance vs. Gate-Source Voltage

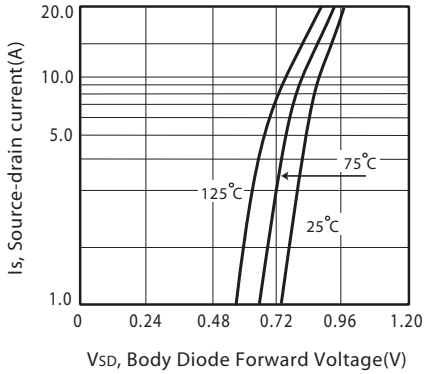


Figure 8. Body Diode Forward Voltage Variation with Source Current

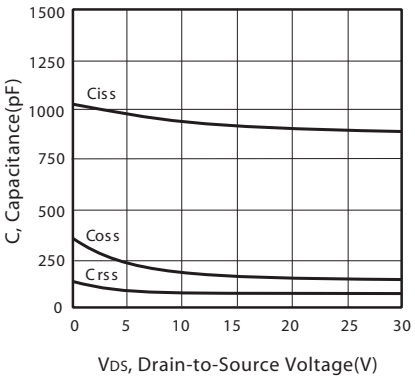


Figure 9. Capacitance

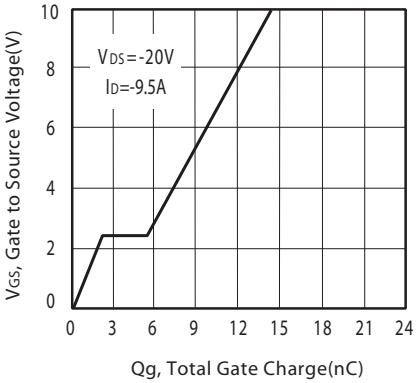


Figure 10. Gate Charge

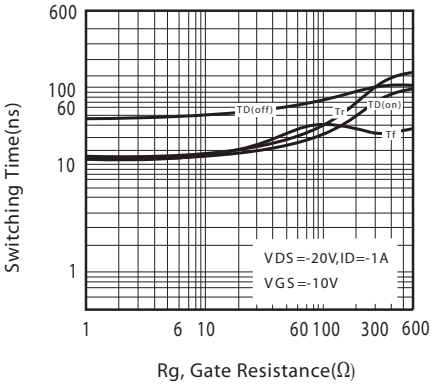


Figure 11. switching characteristics

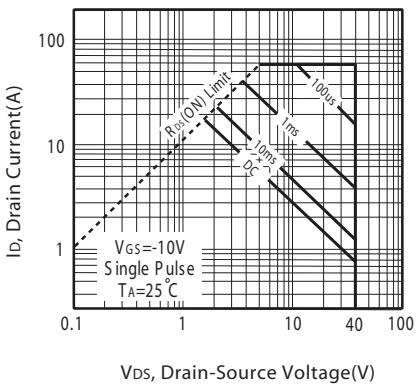
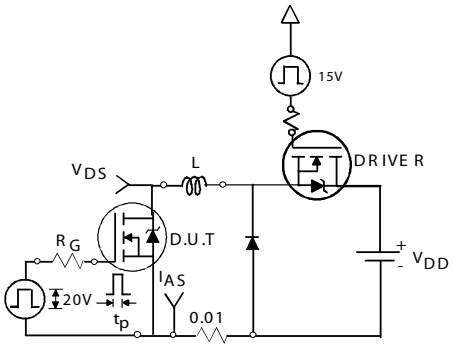
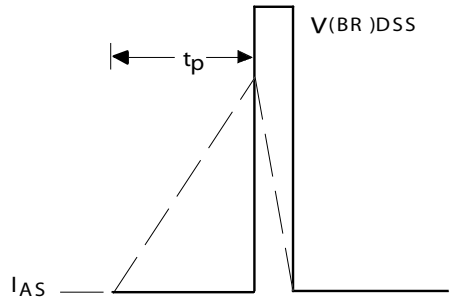


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

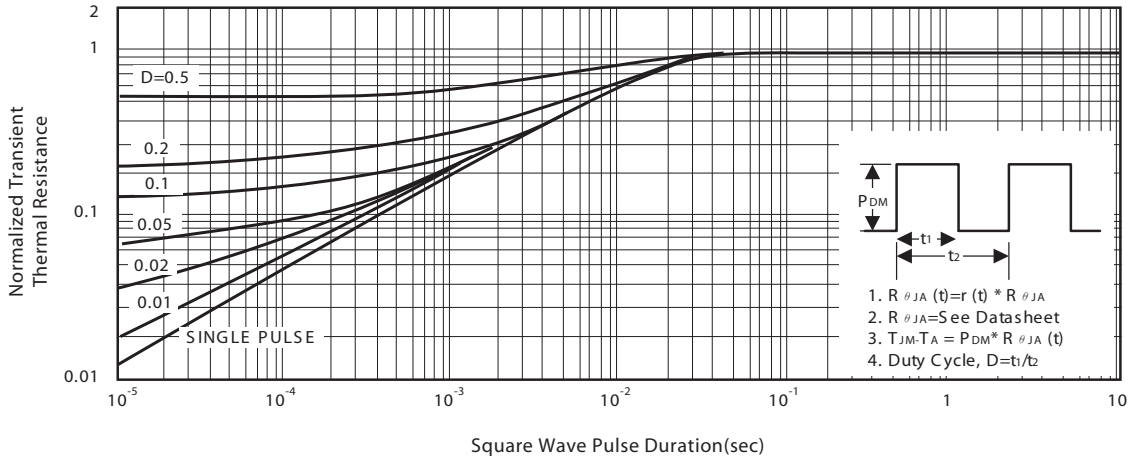
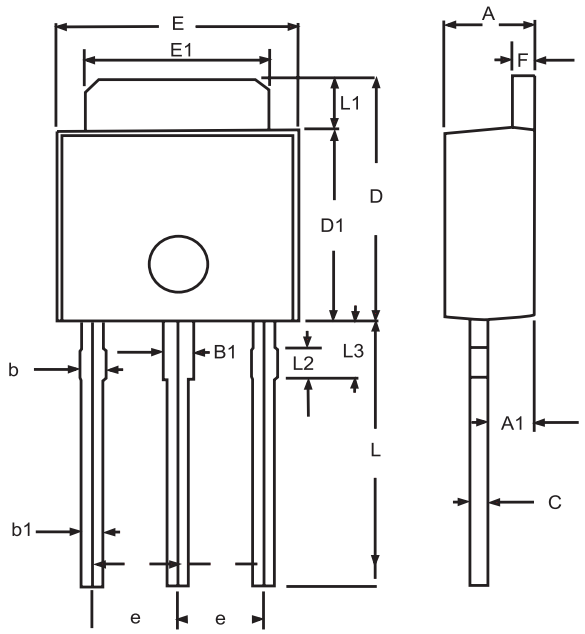


Figure 14. Normalized Thermal Transient Impedance Curve

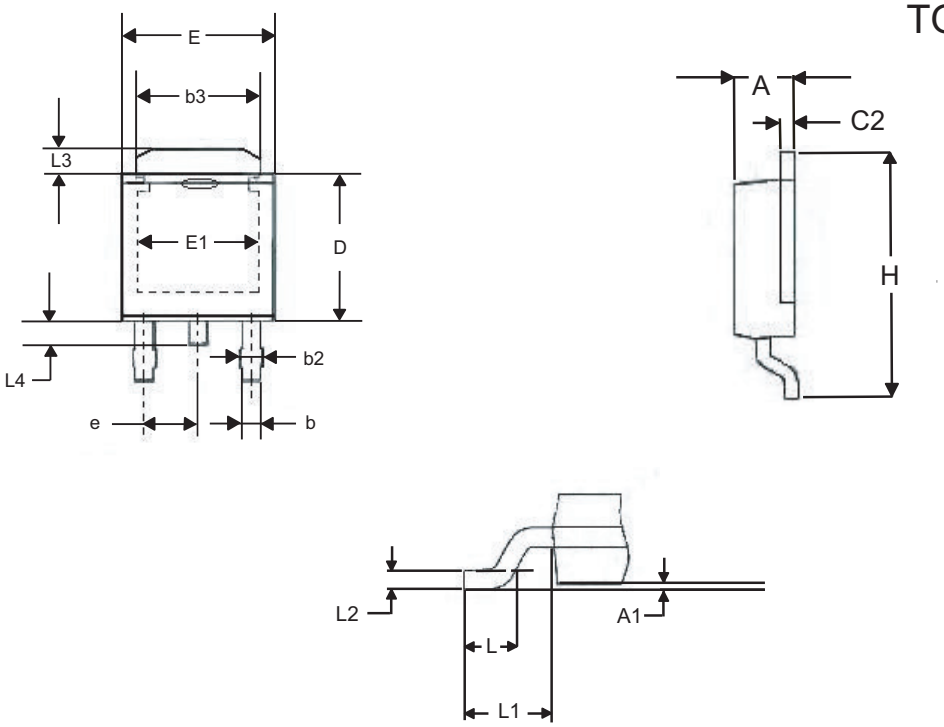
PACKAGE OUTLINE DIMENSIONS

TO-251



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.095
A1	1.100	1.300	0.043	0.051
B1	0.650	1.050	0.026	0.041
b	0.500	0.900	0.020	0.035
b1	0.400	0.800	0.016	0..32
C	0.400	0.600	0.016	0.024
D	6.700	7.300	0.264	0.287
D1	5.400	5.650	0.213	0.222
E	6.40	6.650	0.252	0.262
e	2.100	2.500	0.083	0.098
F	0.400	0.600	0.016	0.024
L	7.000	8.000	0.276	0.315
L1	1.300	1.700	0.051	0.067
L2	0.700	0.900	0.028	0.035
L3	1.400	1.800	0.055	0.071

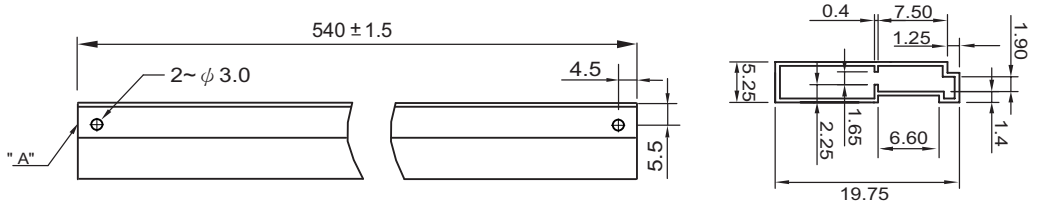
TO-252



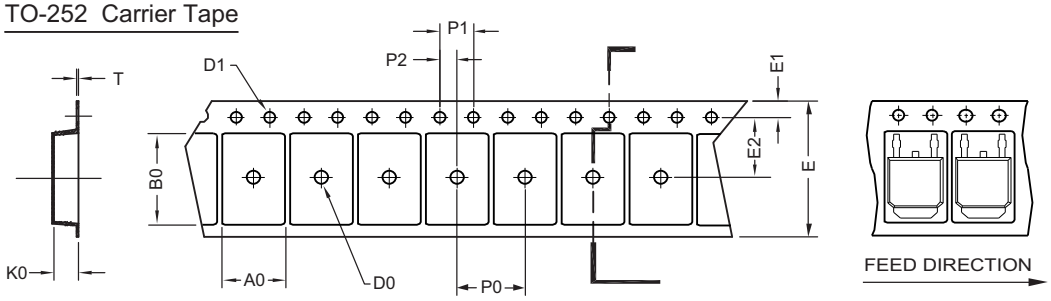
SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.210	2.387	0.087	0.094
C2	0.483	0.584	0.019	0.023
b	0.814	0.889	0.032	0.035
b2	0.864	1.092	0.034	0.043
b3	5.232	5.436	0.206	0.214
L2	0.508	REF.	0.020	REF.
D	6.000	6.200	0.236	0.244
E	6.400	6.604	0.252	0.260
E1	4.902	5.004	0.193	0.197
e	2.290	BSC	0.090	BSC
H	9.601	10.210	0.378	0.402
A1	0.010	0.127	0.0004	0.005
L4	0.066	0.940	0.026	0.037
L	1.397	1.651	0.055	0.065
L1	2.743	REF.	0.108	REF.
L3	1.100	REF.	0.043	REF.

TO251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



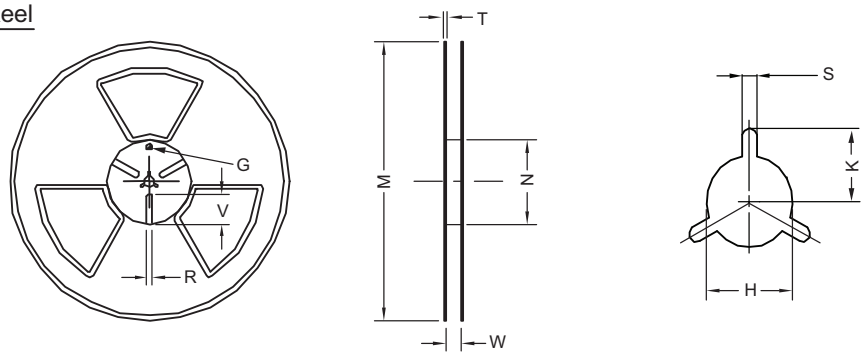
TO-252 Carrier Tape



UNIT:㎜

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 ㎜)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ2	φ1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:㎜

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 ㎜	φ 330	φ330 ± 0.5	φ97 ± 1.0	17.0 + 1.5 - 0	2.2	φ13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---